

# 2SK3662

Switching Regulator, DC-DC Converter, Motor Drive Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 9.4 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 55 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 60 \text{ V}$ )
- Enhancement-mode:  $V_{th} = 1.3 \text{ to } 2.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	60	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	60	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	35	A
	Pulse (Note 1)	$I_{DP}$	105	
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )		$P_D$	35	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	204	mJ
Avalanche current		$I_{AR}$	35	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	3.5	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.57	$^\circ\text{C}/\text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C}/\text{W}$

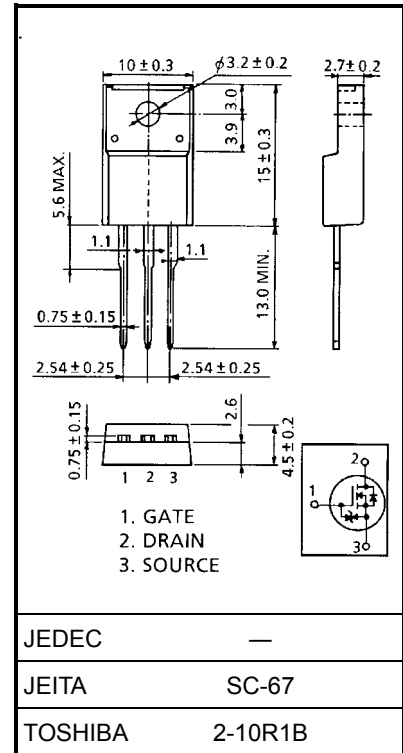
Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = 25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 227 \text{ }\mu\text{H}$ ,  $I_{AR} = 35 \text{ A}$ ,  $R_G = 25 \text{ }\Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 1.9 g (typ.)

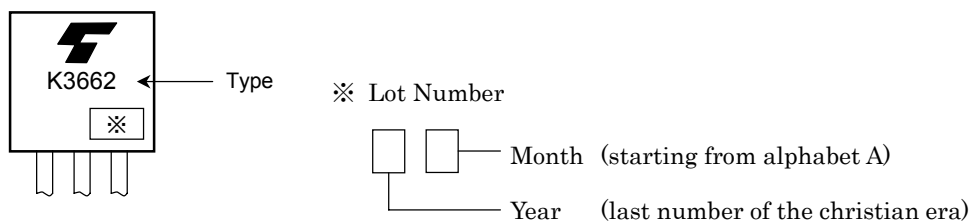
## Electrical Characteristics (Ta = 25°C)

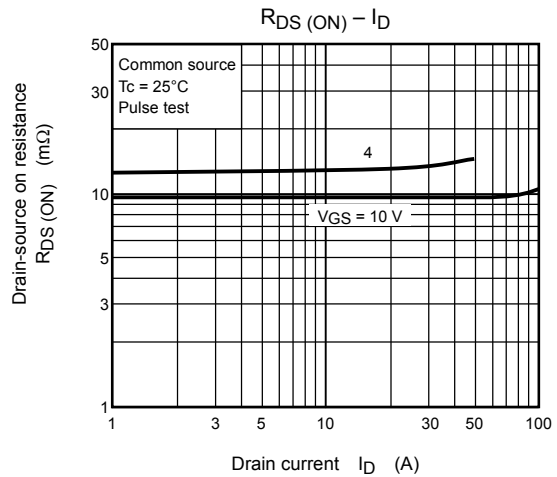
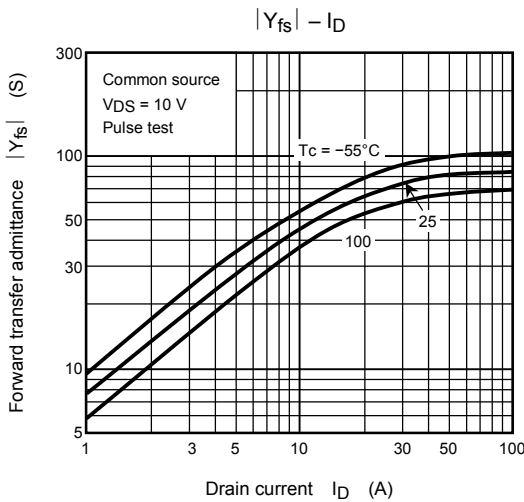
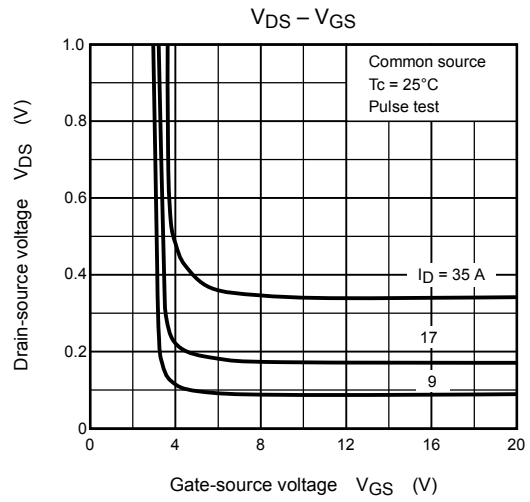
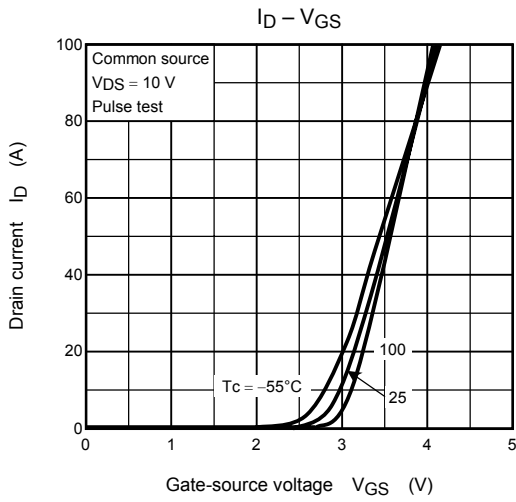
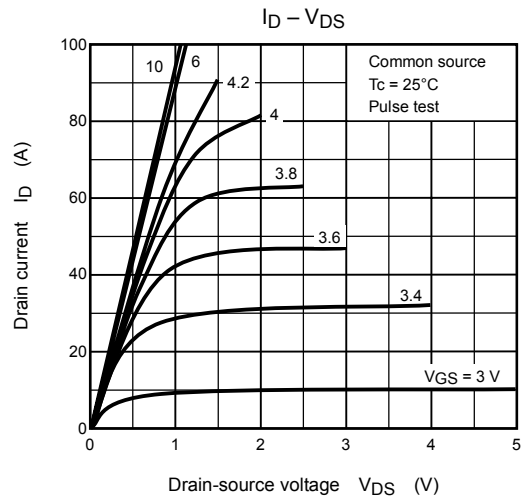
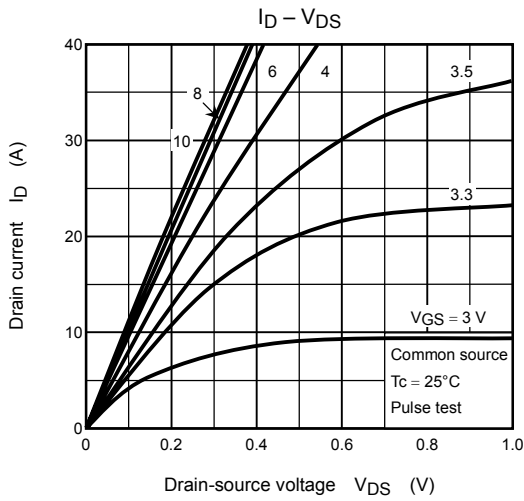
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	60	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	40	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.3	—	2.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 18\text{ A}$	—	12.5	19	$\text{m}\Omega$
			$V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	9.4	12.5	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 18\text{ A}$	28	55	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	5120	—	pF
Reverse transfer capacitance		$C_{rss}$		—	300	—	
Output capacitance		$C_{oss}$		—	500	—	
Switching time	Rise time	$t_r$		—	6	—	ns
	Turn-on time	$t_{on}$		—	19	—	
	Fall time	$t_f$		—	20	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$	—	115	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	—	91	—	nC
Gate-source charge		$Q_{gs}$		—	70	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	21	—	

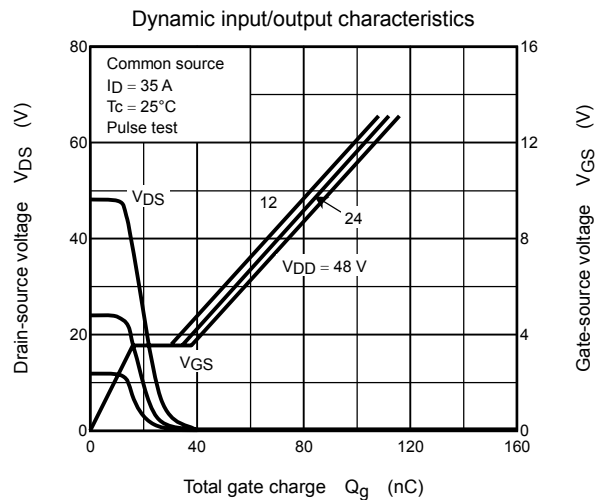
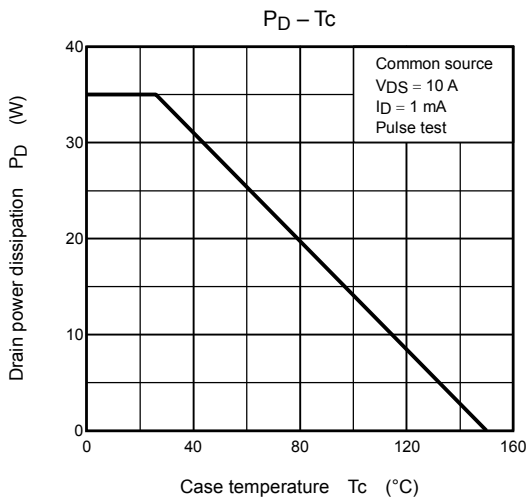
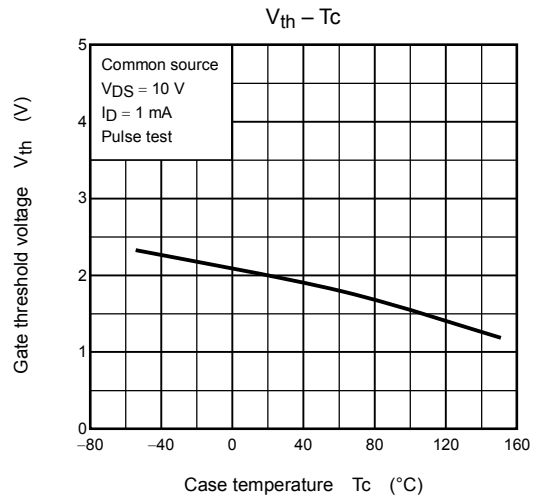
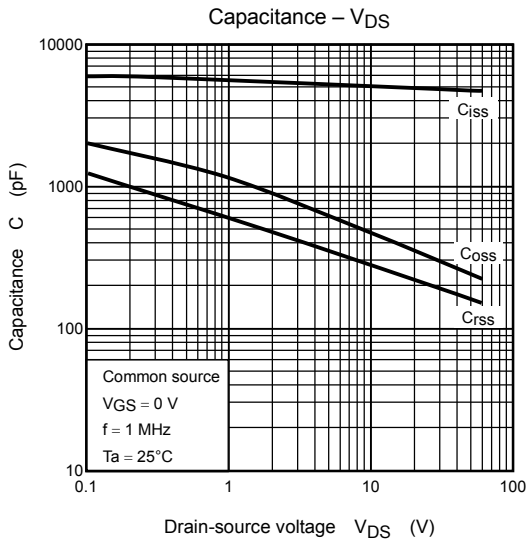
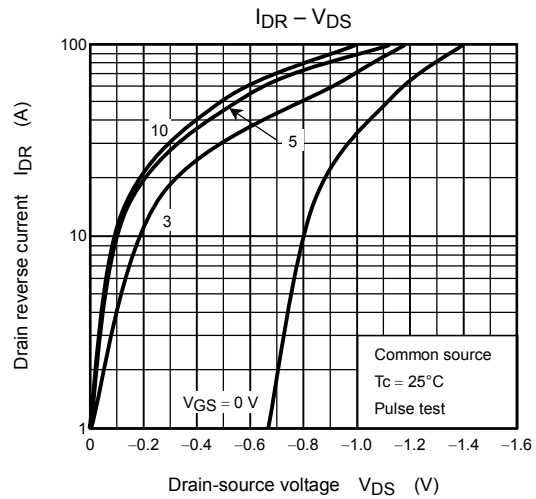
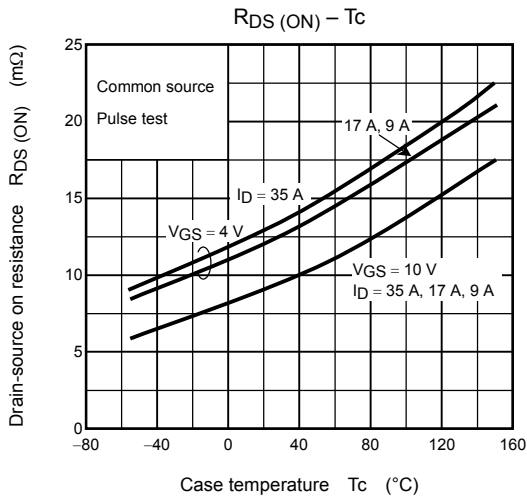
## Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

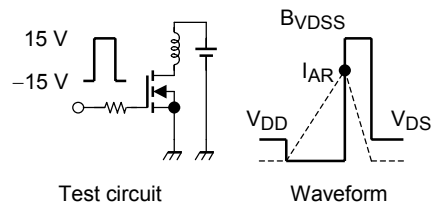
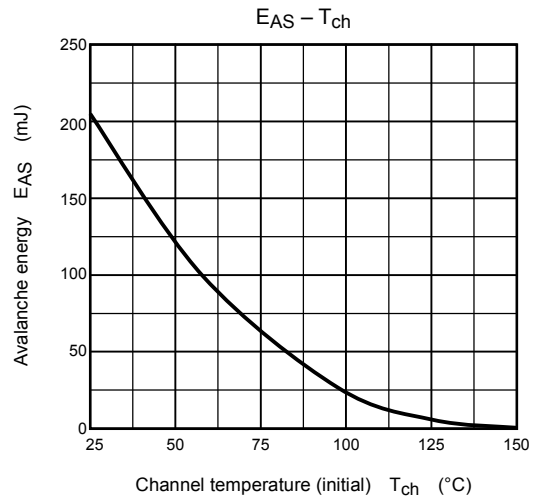
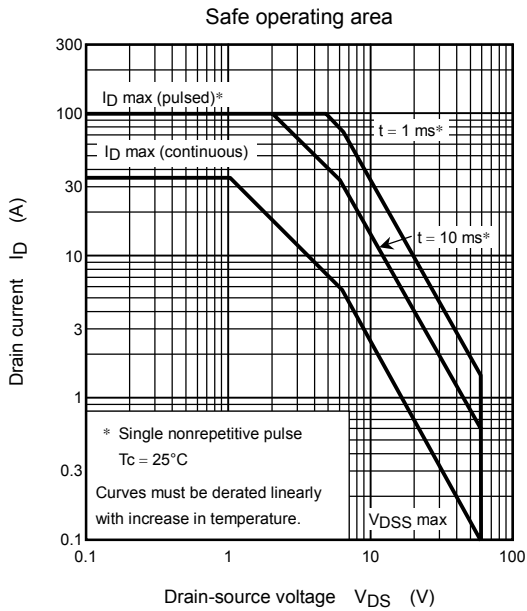
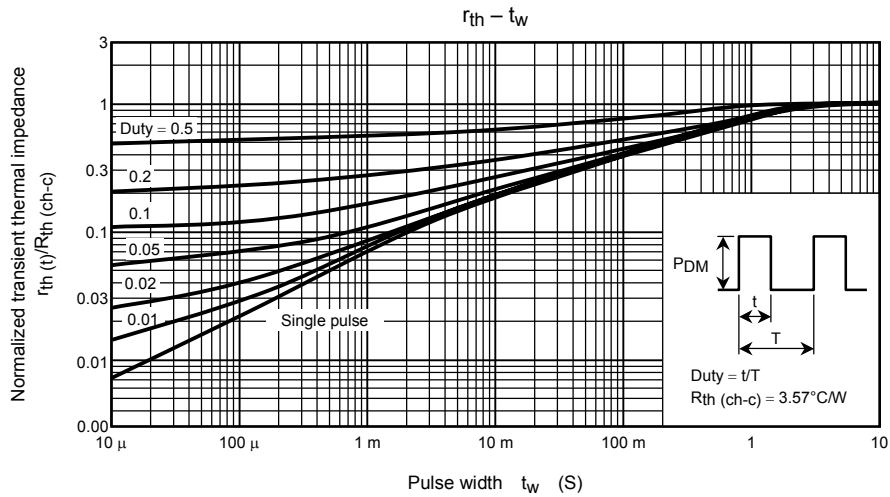
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	35	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	105	A
Forward voltage (diode)	$V_{DS2F}$	$I_{DR1} = 35\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 35\text{ A}, V_{GS} = 0\text{ V},$	—	60	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	58	—	nC

## Marking









$$R_G = 25 \Omega$$

$$V_{DD} = 25 \text{ V}, L = 227 \mu\text{H}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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